

## New method of porous Ge layer fabrication: structure and optical properties

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Porous germanium films were produced by selective removal of the GeO<sub>2</sub> matrix from the GeO<sub>2</sub>/Ge-NCs heterolayer in deionized water or HF. On the basis of Raman and infrared spectroscopy data it was supposed Ge-NCs heterolayers. The kinetics of air oxidation of amorphous porous Ge layers was investigated by scanning ellipsometry. Spectral ellipsometry allowed estimating the porosity of amorphous and crystalline porous Ge layers, which was ~ 70% and ~ 80%, respectively.

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